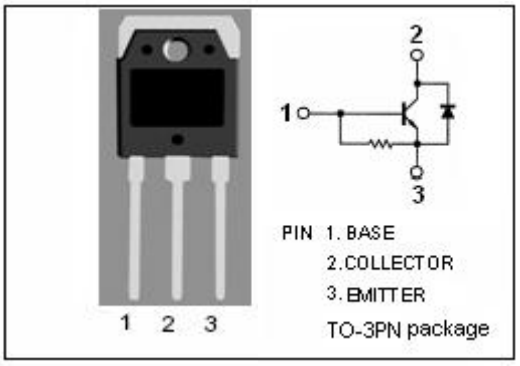
isc Silicon NPN Power Transistor 2SC3479

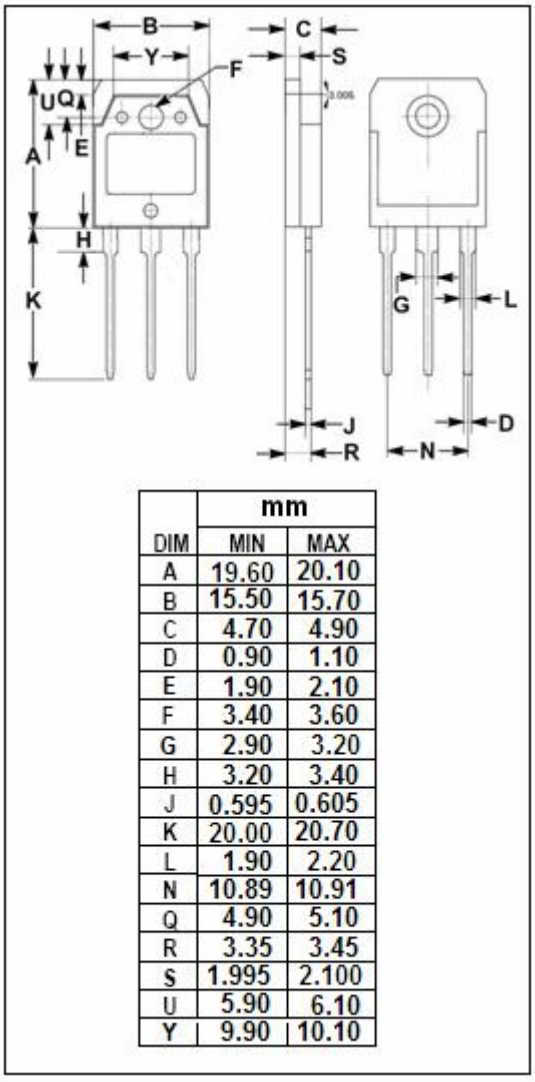
DESCRIPTION

- High Breakdown Voltage-
  : V_{CBO}= 1500V (Min)
- High Switching Speed
- High Reliability
- Built-in Damper Diode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Designed for high definition CRT display horizontal deflection output applications.



DIM	mm MIN	MAX
A	19.60	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	20.00	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.10
Y	9.90	10.10

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current- Continuous	2.5	A
I_{CP}	Collector Current-Pulse	8	A
P_C	Collector Power Dissipation @ T_C=25℃	80	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 5mA; R_{BE}= ∞	800			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 5mA; I_E= 0	1500			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 200mA; I_C= 0	7			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 2.5A; I_B= 0.8A			8.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 2.5A; I_B= 0.8A			1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 800V; I_E= 0			10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 4V; I_C= 0	40		130	mA
h_{FE}	DC Current Gain	I_C= 0.5A; V_{CE}= 5V	8			
V_{ECF}	C-E Diode Forward Voltage	I_F= 2.5A			2.0	V
f_T	Current-Gain—Bandwidth Product	I_C= 0.5A; V_{CE}= 10V		3		MHz
t_f	Fall Time	I_C= 2A, I_{B1}= 0.4A; I_{B2}= -0.8A			0.3	μs